

PATENT
(5298-03500/PM99021)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Lau

Serial No. 09/476,669

Filed: December 30, 1999

For: METHOD FOR FORMING A
METALLIZATION STRUCTURE IN
AN INTEGRATED CIRCUIT

Do Not Enter

OK to Enter *PL 12/14/02* **AMENDMENT; RESPONSE AFTER FINAL REJECTION PURSUANT TO 37 CFR § 1.116**

Box AF
Commissioner for Patents
Washington, D.C. 20231

Dear Sir/Madam:

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DEC 11 2002
TC 1700

This paper is submitted in response to the Office Action mailed August 30, 2002 to further highlight reasons why the application is in condition for allowance.

Please amend the case as follows.

IN THE SPECIFICATION

Please replace pg. 20, line 22 - pg. 21, line 7, with the amended paragraph below. A "marked-up" version of each amendment is included in **Attachment A**.

To resolve these problems, the present method is preferably configured to deposit metal atoms with sufficient force to sputter previously deposited metal away from the ion impact area. The impact energy of the metal ions on the microelectronic topography is largely determined by the